

# FORWARD AS ONE SEMICON® EUROPA



## Advancements in Wireless Tech

### Frugal Artificial Intelligence For Edge Devices



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#### Abstract

Considering the huge demand for edge devices, frugality has become a critical challenge and still require deep innovation . Thomas Signamarcheix, CEA-Leti's Vice President Strategic Development, will present how new hardware could provide disruptive solutions for edge devices and especially event based sensors .

#### Biography

Joined CEA-Leti in 2008 and was named manager of a research laboratory on substrates engineering in 2011. From 2015 to 2019, he was promoted to business development management for Leti's Silicon Component Division and Architecture and Embedded Software Division. Also, as Key Account Manager of several strategic collaborations, he directly managed a wide range of activity (semiconductor, alternative energy, sensor, radio-frequency, etc.) promoting innovation at both hardware and architectures level. He has served as vice president of CEA-Leti's strategic development since 2020, managing Leti's strategic program (Quantum Electronic, Artificial Intelligence, wearable healthcare devices and mixed reality) and strategic partnerships. He has a Ph.D. degree in the physics of semiconductor devices from Grenoble Institute of Technology (INPG).

## Engineered Substrates and Materials for 5G



C. Roda Neve  
R&D Program Manager  
SOITEC, Hasselt, Belgium



### Abstract

information coming soon

### Biography

Cesar Roda Neve was born in Madrid, Spain, in 1975. He received the Msc. Engineer degree from the ICAI Universidad Pontificia de Comillas, Madrid, Spain, in 2000. In 2012, he received the Ph.D. degree in engineering sciences from the Université catholique de Louvain (UCL), Belgium. From 2004 to 2006, he was with the Electronics Department of the University Carlos III of Madrid, Spain, where he worked on ROF links and optoelectronic devices. From 2006 to 2012, he joined the Microwave Laboratory at the Université catholique de Louvain (UCL), Belgium, where he worked on the characterization and application of Si-based substrates for RF integration, in particular the use of HR-Si, HRSOI, and trap-rich HR-SOI substrates, non-linearities and parasitic effects. From 2013 to 2016, he was with the 3D and Optical Technology group at IMEC, where he worked on signal integrity, power delivery networks and RF modeling with special attention to 3D stacking and packaging. From 2016 to 2020, he worked at M3Systems Belgium as project manager for GPS, interferences and satellite related projects. In 2021 he joined SOITEC Belgium as R&D Program Manager. His research interest are new applications for SOI substrates for RF, with focus in 5G and 6G communications.

## Opportunities and challenges of high-throughput 3D metrology equipment for semiconductor process control



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### Abstract

In the semiconductor industry, Moore's law comes with increasing and complex demands and the need for advanced process control metrology. Traditional metrologies like OCD or CD-SEM lose sensitivity due to diminishing interaction volume. A metrology technique that thrives in this regime is Atomic Force Microscopy (AFM).

AFM is a technique currently used in process and integration development because it can provide reference-level local imaging and metrology. Unique strength over competing metrology techniques includes the potential for undistorted, local high-resolution information. Two factors are currently limiting deployment of AFM tools for inline process control: 1) ability to fully resolve deep, narrow structures and 2) throughput compatible with other metrologies currently deployed in High Volume Manufacturing (HVM). Here, we discuss the advantages of a multi-head AFM system with miniaturized high-speed AFMs working in parallel. In addition, we extend traditional AFM techniques to selective imaging and metrology of subsurface 3D structures and show a path to enabling Overlay metrology through opaque hard mask layers.

### Biography

Dr. Hamed Sadeghian

Co-Founder, President and CEO of Nearfield Instruments

Hamed Sadeghian received his PhD (Cum Laude) in 2010 from Delft University of Technology. Four years later he received an MBA degree from the Vlerick Business School in Belgium. He is the founder (2001) of Jahesh Poulad Co., a manufacturer of mechanical equipment.

Hamed worked as a system architect and led a team of thirty researchers in nano-optomechanics instrumentation at TNO in Delft from 2011 to 2018. In 2016 he co-founded Nearfield Instruments and is currently president & chief technology officer at this scale-up that recently sold its first metrology instrument to a high-end chip manufacturer.

Hamed Sadeghian is a part time associate Professor at the Technical University of Eindhoven. He holds more than 70 patents, and published over 100 peer-reviewed technical papers. He is currently also a principal scientist and Kruyt member of TNO.